

# 0150SC-1250M

# 1250Watts, 125 Volts, Class AB 150 to 160 MHz Silicon Carbide SIT

#### PRELIMINARY SPECIFICATION

### **GENERAL DESCRIPTION**

The 0150SC-1250M is a Common Gate N-Channel Class AB SILICON CARBIDE STATIC INDUCTION TRANSISTOR (SIT) capable of providing 1250 Watts minimum of RF power from 150 to 160 MHz. The transistor is designed for use in High Power Amplifiers supporting applications such as VHF Weather Radar and Long Range Tracking Radar. The device is the first in a series of High Power Silicon Carbide Transistors from Microsemi PPG.

CASE OUTLINE 55KT FET (Common Gate) See outline drawing

#### ABSOLUTE MAXIMUM RATINGS

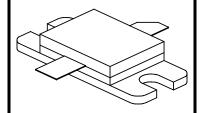
**Voltage and Current** 

 $\begin{array}{ll} \text{Drain-Source ($V_{DSS}$)} & 250 \text{ V} \\ \text{Gate-Source ($V_{GS}$)} & -1 \text{V} \\ \text{Drain Current (Idg)} & 35 \text{A} \\ \end{array}$ 

**Temperatures** 

Storage Temperature -65 to +150°C Operating Junction Temperature +250°C





#### **ELECTRICAL CHARACTERISTICS @ 25°C**

SYMBOL	CHARACTERISTICS	TEST CONDITIONS	MIN	TYP	MAX	UNITS
$I_{dss1}$	Drain-Source Leakage Current	$V_{GS} = -15V, V_{DG} = 95V$			750	μΑ
$I_{gss}$	Gate-Source Leakage Current	$V_{GS} = -20V, V_{DS} = 0V$			50	μΑ
$\theta_{ m JC}^{-1}$	Thermal Resistance	Pout=1250W			0.15	°C/W

### $FUNCTIONAL\ CHARACTERISTICS\ @\ 25^{\circ}C,\ Vdd=125V,\ I_{dq(avg)}=500\ mA,\ Freq=155\ MHz,$

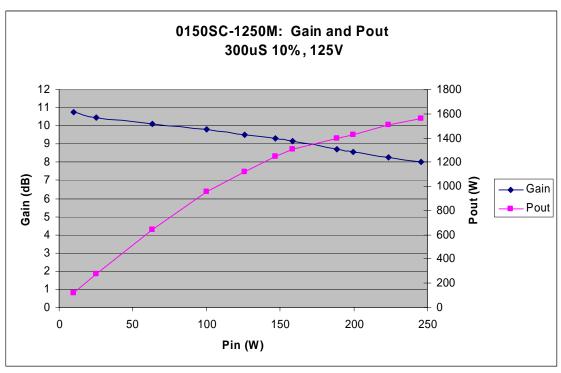
$G_{PG}$	Common Gate Power Gain	$P_{out} = 1250 \text{ W}, \text{Pulsed}$	9.0	9.5		dB
$P_{in}$	Input Power	Pulse Width = $300us$ , DF = $10\%$		150	160	W
$\eta_{\mathrm{d}}$	Drain Efficiency	$F = 155 \text{ MHz}, P_{\text{out}} = 1250 \text{W}$	60			%
Ψ	Load Mismatch	$F = 155 \text{ MHz}, P_{\text{out}} = 1250 \text{W}$			10:1	
Po +1dB	Power Output – Higher Drive	F = 155 MHz, Pin = 190 W		1400		W
Vsg	Source-Gate Voltage	Set for Idq(avg) = 500 mA	3.0		10.0	Volts

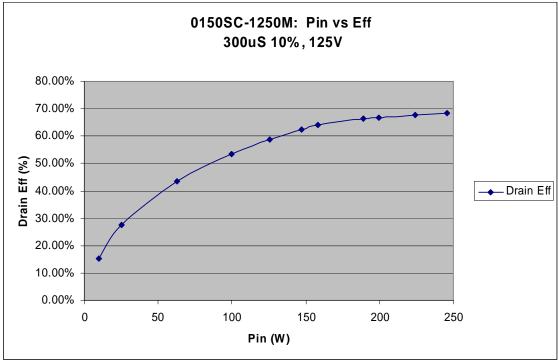
Dec 2008





# **Typical RF Performance Curve**

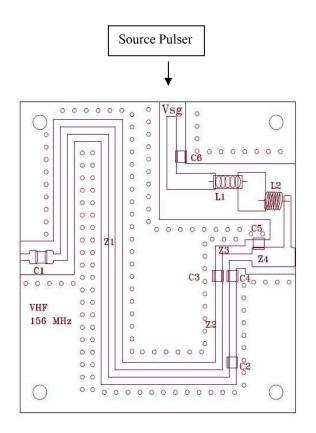


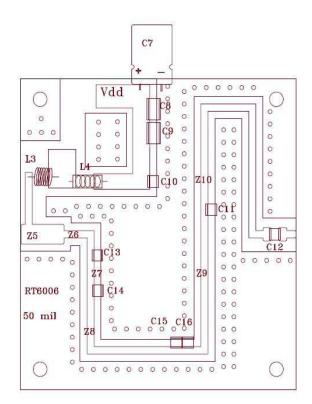




## 0150SC-1250M

## **Test Circuit Information**





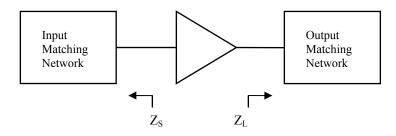
0150SC-1250M Test Circuit Component Designations and Values

Part	Description	Part	Description
C1, C6,	2200pF Chip Capacitor (ATC 700B)	L1, L4	Ferrite Coil Inductor
C10, C12			
C2	12pF Chip Capacitor (ATC 100B)	Z1	71 x 5450 mils (W x L)
C3	56pF Chip Capacitor (ATC 100B)	Z2	71 x 830 mils (W x L)
C4, 14	68pF Chip Capacitor (ATC 100B)	Z3	71 x 435 mils (W x L)
C5	100pF Chip Capacitor (ATC 100B)	Z4, Z5	190 x 430 mils (W x L)
C7	1000uF 160V Electrolytic Capacitor	Z6	71 x 555 mils (W x L)
C8, C9	1uF Chip Capacitor	<b>Z</b> 7	71 x 340 mils (W x L)
C11, C15	15pF Chip Capacitor (ATC 100B)	Z8	71 x 1285 mils (W x L)
C13	47pF Chip Capacitor (ATC100B)	Z9	71 x 1520 mils (W x L)
C16	22pF Chip Capacitor (ATC100B)	Z10	71 x 2810 mils (W x L)
PCB	Rogers 6006, $\varepsilon_r$ =6.15, 50mils, 1oz		
L2, L3	7 Turns, 18AWG, IDIA 0.2"	Note:	All Z length dimensions include bends





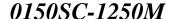
# **Impedance Information**



## **Typical Impedance Values**

Frequency (MHz)  $Z_{\rm S}(\Omega)$  $Z_L(\Omega)$ 0.7 - j0.52 3.7 + j3.8156

<sup>\*</sup>  $V_{DD}$  = 125V,  $I_{DQ(avg)}$  = 500mA,  $P_{out}$  = 1250W \* Pulse Format: 300 $\mu$ s, 10% Long Term Duty Factor





## Case Outline 55 KT FET

